

NOTICE

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Integrated Device Technology, Inc.

CMOS STATIC RAM
256K (32K x 8-BIT)

IDT71256S
IDT71256L

FEATURES:

- Optimized for fast RISC processors including the IDT79R3000
- High-speed address/chip select time
 - Military: 25/30/35/45/55/70/85/100/120/150ns (max.)
 - Commercial: 20/25/30/35/45ns (max.)
- Low-power operation
- Battery Backup operation — 2V data retention
- Produced with advanced high-performance CEMOS™ technology
- Single 5V(±10%) power supply
- Input and output directly TTL-compatible
- Static operation: no clocks or refresh required
- Available in standard 28-pin (600 mil) CERDIP, 28-pin (300 or 600 mil) plastic DIP, 28-pin (300 mil) ceramic sidebraze DIP, 28-pin (330 mil) SOIC and (300 mil) SOJ, 28-pin CERPACK, 32-pin LCC or PLCC, 28-pin LCC
- Military product compliant to MIL-STD-883, Class B
- This function is listed as Standard Military Drawing #5962-8852 (L-Power) and #5962-8862 (S-Power)

DESCRIPTION:

The IDT71256 is a 262,144-bit high-speed static RAM organized as 32K x 8. It is fabricated using IDT's high-performance, high-reliability CEMOS technology. This state-

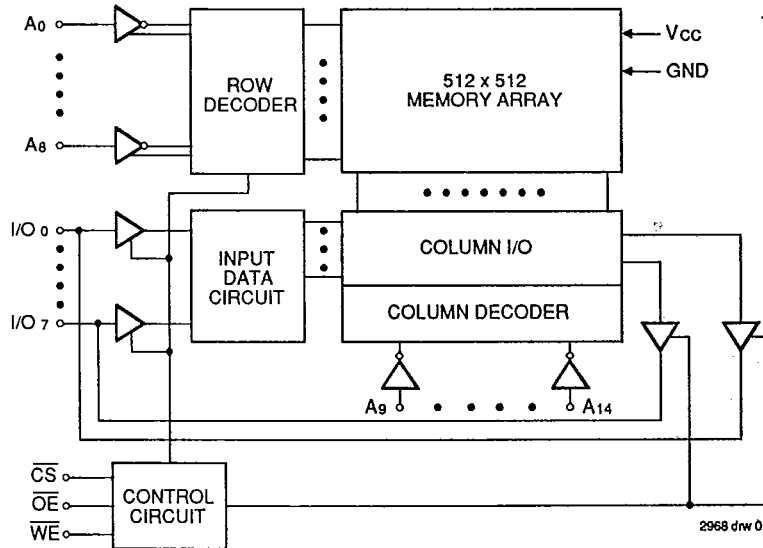
of-the-art technology, combined with innovative circuit design techniques, provides a cost effective alternative to bipolar and fast NMOS memories. Timing parameters have been specified to meet the speed demands of the fastest IDT79R3000 RISC processors.

Address access times as fast as 20ns are available with power consumption of only 350mW (typ.). The circuit also offers a reduced power standby mode. When \overline{CS} goes high, the circuit will automatically go to, and remain in, a low-power standby mode as long as \overline{CS} remains high. In the full standby mode, the low-power device consumes less than 15µW, typically. This capability provides significant system level power and cooling savings. The low power (L) version also offers a battery backup data retention capability where the circuit typically consumes only 5µW when operating off a 2V battery.

The IDT71256 is packaged in a 28-pin (330 mil) gull-wing or (300 or 350 mil) J-bend SOIC, a 28-pin 600 mil CERDIP, 28-pin (300 or 600 mil) plastic DIP, 28-pin (300 mil) ceramic sidebraze DIP, 28-pin CERPACK, 32-pin LCC or PLCC, 28-pin LCC, providing high board-level packing densities.

The IDT71256 military RAM is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

FUNCTIONAL BLOCK DIAGRAM



CEMOS is a trademark of Integrated Device Technology, Inc.

MILITARY AND COMMERCIAL TEMPERATURE RANGES

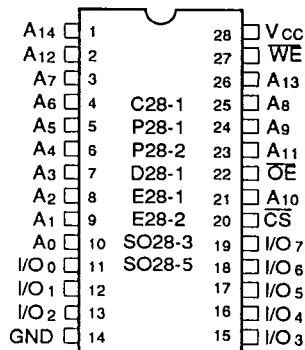
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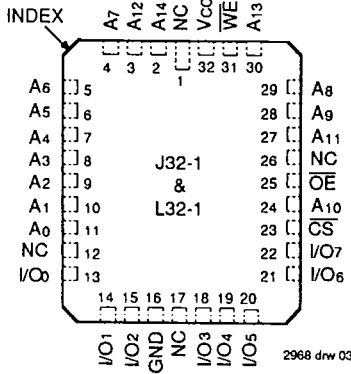
IDT71256 CMOS STATIC RAM 256K (32K x 8-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

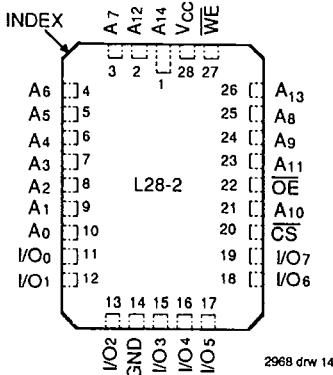
PIN CONFIGURATIONS



DIP/SOJ/SOIC TOP VIEW



32-Pin LCC/PLCC TOP VIEW



28-Pin LCC TOP VIEW

PIN DESCRIPTIONS

Name	Description
A0-A14	Addresses
I/O0-I/O7	Data Input/Output
CS	Chip Select
WE	Write Enable
OE	Output Enable
GND	Ground
VCC	Power

2968 tbl 01

TRUTH TABLE⁽¹⁾

WE	CS	OE	I/O	Function
X	H	X	High-Z	Standby (Isb)
X	VHC	X	High-Z	Standby (Isb1)
H	L	H	High-Z	Output Disable
H	L	L	DOUT	Read
L	L	X	DIN	Write

NOTE:

1. H = VIH, L = VIL, X = Don't Care

2968 tbl 02

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Com'l.	Mil.	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	1.0	1.0	W
IOUT	DC Output Current	50	50	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2968 tbl 03

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 0V	11	pF
COUT	Output Capacitance	VOUT = 0V	11	pF

NOTE:

1. This parameter is determined by device characterization, but is not production tested.

2968 tbl 04

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IDT71256 CMOS STATIC RAM 256K (32K x 8-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Temperature	GND	Vcc
Military	-55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

2968 tbl 05

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V _{IH}	Input High Voltage	2.2	—	6.0	V
V _{IL}	Input Low Voltage	-0.5 ⁽¹⁾	—	0.8	V

2968 tbl 06

NOTE:

- V_{IL} (min.) = -3.0V for pulse width less than 20ns.

DC ELECTRICAL CHARACTERISTICS^(1, 2)

(VCC = 5.0V ± 10%, V_{LC} = 0.2V, V_{HC} = VCC - 0.2V)

Symbol	Parameter	Power	71256x20		71256x25		71256x30		71256x35		Unit
			Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
I _{CC}	Dynamic Operating Current CS ≤ V _{IL} , Outputs Open VCC = Max., f = f _{MAX} ⁽³⁾	S	155	—	145	150	170	180	155	165	mA
		L	135	—	115	130	145	160	130	145	
I _{SB}	Standby Power Supply Current (TTL Level) CS ≥ V _{IH} , VCC = Max., Outputs Open, f = f _{MAX} ⁽³⁾	S	20	—	20	20	20	20	20	20	mA
		L	3	—	3	3	3	3	3	3	
I _{SB1}	Full Standby Power Supply Current (CMOS Level) CS ≥ V _{HC} , VCC = Max., V _{LC} ≥ V _{IN} ≥ V _{HC} , f = 0	S	15	—	15	20	15	20	15	20	mA
		L	0.4	—	0.4	1.5	0.4	1.5	0.4	1.5	

Symbol	Parameter	Power	71256x45		71256x55		71256x70		71256x85 ⁽⁵⁾		71256x100		Unit
			Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
I _{CC}	Dynamic Operating Current CS ≤ V _{IL} , Outputs Open VCC = Max., f = f _{MAX} ⁽³⁾	S	140	150	—	150	—	150	—	150	—	150	mA
		L	120	135	—	125	—	125	—	125	—	125	
I _{SB}	Standby Power Supply Current (TTL Level) CS ≥ V _{IH} , VCC = Max., Outputs Open, f = f _{MAX} ⁽³⁾	S	20	20	—	20	—	20	—	20	—	20	mA
		L	3	3	—	3	—	3	—	3	—	3	
I _{SB1}	Full Standby Power Supply Current (CMOS Level) CS ≥ V _{HC} , VCC = Max., V _{LC} ≥ V _{IN} ≥ V _{HC} , f = 0	S	15	20	—	20	—	20	—	20	—	20	mA
		L	0.4	1.5	—	1.5	—	1.5	—	1.5	—	1.5	

NOTES:

- All values are maximum guaranteed values.
- An "x" in part numbers indicate power rating (S or L).
- f_{MAX} = 1/1T_{RC}.
- Standby current mode not available at 20ns.
- Also available: 120 and 150 ns military devices.

2968 tbl 07

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AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1 and 2

2968 tbl 08

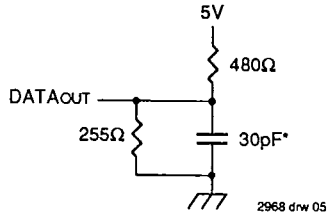


Figure 1. Output Load

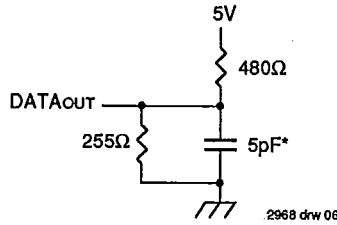


Figure 2. Output Load
(for tCLZ, tOLZ, tCHZ, tOHZ, tLOW, tWHZ)

*Includes scope and jig capacitances



DC ELECTRICAL CHARACTERISTICS

VCC = 5.0V ± 10%

Symbol	Parameter	Test Condition	IDT71256S			IDT71256L			Unit	
			Min.	Typ.	Max.	Min.	Typ.	Max.		
ILI	Input Leakage Current	VCC = Max., VIN = GND to VCC	MIL. COM'L.	—	—	10 5	—	—	5 2	μA
ILO	Output Leakage Current	VCC = Max., CS = VIH, VOUT = GND to VCC	MIL. COM'L.	—	—	10 5	—	—	5 2	μA
VOL	Output Low Voltage	IOL = 8mA, VCC = Min.		—	—	0.4	—	—	0.4	V
		IOL = 10mA, VCC = Min.		—	—	0.5	—	—	0.5	
VOH	Output High Voltage	IOH = -4mA, VCC = Min.		2.4	—	—	2.4	—	—	V

2968 tbl 09

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DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES

(L Version Only) $V_{LC} = 0.2V$, $V_{HC} = V_{CC} - 0.2V$

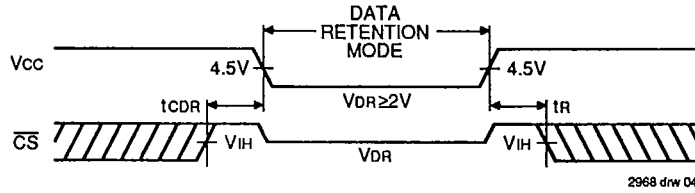
Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾ V _{CC} @		Max. V _{CC} @		Unit
				2.0V	3.0V	2.0V	3.0V	
V _{DR}	V _{CC} for Data Retention	—	2.0	—	—	—	—	V
I _{CCDR}	Data Retention Current	$\overline{CS} \geq V_{HC}$ $V_{IN} \geq V_{HC}$ or $\leq V_{LC}$	—	—	—	200	800	μA
			MIL. COM'L.	—	—	—	120	200
t _{CDR}	Chip Deselect to Data Retention Time	$\overline{CS} \geq V_{HC}$ $V_{IN} \geq V_{HC}$ or $\leq V_{LC}$	0	—	—	—	—	ns
t _R ⁽³⁾	Operation Recovery Time		t _{RC} ⁽²⁾	—	—	—	—	ns

NOTES:

1. T_A = +25°C.
2. I_{RC} = Read Cycle Time.
3. This parameter is guaranteed, but not tested.

2968 tbl 10

LOW V_{CC} DATA RETENTION WAVEFORM



IDT71256 CMOS STATIC RAM 256K (32K x 8-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0V ± 10%, All Temperature Ranges)

T-46-23-14

Symbol	Parameter	71256S20 ⁽¹⁾ 71256L20 ⁽¹⁾		71256S25 71256L25		71256S30 71256L30		71256S35 71256L35		71256S45 71256L45		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
		Read Cycle										
t _{RC}	Read Cycle Time	20	—	25	—	30	—	35	—	45	—	ns
t _{AA}	Address Access Time	—	20	—	25	—	30	—	35	—	45	ns
t _{ACS}	Chip Select Access Time	—	20	—	25	—	30	—	35	—	45	ns
t _{CLZ}	Chip Select to Output in Low Z ⁽²⁾	5	—	5	—	5	—	5	—	5	—	ns
t _{OE}	Output Enable to Output Valid	—	10	—	11	—	13	—	15	—	20	ns
t _{OLZ}	Output Enable to Output in Low Z ⁽²⁾	2	—	2	—	2	—	2	—	0	—	ns
t _{CHZ}	Chip Select to Output in High Z ⁽²⁾	—	10	—	11	—	15	—	15	—	20	ns
t _{OHZ}	Output Disable to Output in High Z ⁽²⁾	2	8	2	10	2	12	2	15	—	20	ns
t _{OH}	Output Hold from Address Change	5	—	5	—	5	—	5	—	5	—	ns
Write Cycle												
t _{WC}	Write Cycle Time	20	—	25	—	30	—	35	—	45	—	ns
t _{CW}	Chip Select to End of Write	15	—	20	—	25	—	30	—	40	—	ns
t _{AW}	Address Valid to End of Write	15	—	20	—	25	—	30	—	40	—	ns
t _{AS}	Address Set-up Time	0	—	0	—	0	—	0	—	0	—	ns
t _{WP}	Write Pulse Width	15	—	20	—	25	—	30	—	35	—	ns
t _{WR}	Write Recovery Time	0	—	0	—	0	—	0	—	0	—	ns
t _{WHZ}	Write Enable to Output in High Z ⁽²⁾	—	10	—	11	—	15	—	15	—	20	ns
t _{DW}	Data to Write Time Overlap	11	—	13	—	14 ⁽³⁾	—	15 ⁽³⁾	—	20	—	ns
t _{DH1}	Data Hold from Write Time (\overline{WE})	0	—	0	—	0	—	0	—	0	—	ns
t _{DH2}	Data Hold from Write Time (\overline{CS})	3	—	3	—	3	—	3	—	3	—	ns
t _{OW}	Output Active from End of Write ⁽²⁾	5	—	5	—	5	—	5	—	5	—	ns

- NOTES:
- 0° to +70°C temperature range only.
 - This parameter guaranteed but not tested.
 - For the 0°C to +70°C temperature range,
 - 30ns speed grade, t_{OW} = 14ns.
 - 35ns speed grade, t_{OW} = 15ns.
 For the -55°C to +125°C temperature range,
 - 30ns speed grade, t_{OW} = 17ns.
 - 35ns speed grade, t_{OW} = 18ns.

2968 tbl 11



AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0V ± 10%, All Temperature Ranges)

Symbol	Parameter	71256S55 ⁽¹⁾ 71256L55 ⁽¹⁾		71256S70 ⁽¹⁾ 71256L70 ⁽¹⁾		71256S85 ⁽¹⁾ 71256L85 ⁽¹⁾		71256S100 ⁽³⁾ 71256L100 ⁽³⁾		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
t _{RC}	Read Cycle Time	55	—	70	—	85	—	100	—	ns
t _{AA}	Address Access Time	—	55	—	70	—	85	—	100	ns
t _{ACS}	Chip Select Access Time	—	55	—	70	—	85	—	100	ns
t _{CLZ}	Chip Select to Output in Low Z ⁽²⁾	5	—	5	—	5	—	5	—	ns
t _{OE}	Output Enable to Output Valid	—	25	—	30	—	35	—	40	ns
t _{OLZ}	Output Enable to Output in Low Z ⁽²⁾	0	—	0	—	0	—	0	—	ns
t _{CHZ}	Chip Select to Output in High Z ⁽²⁾	—	25	—	30	—	35	—	40	ns
t _{OHZ}	Output Disable to Output in High Z ⁽²⁾	0	25	0	30	—	35	—	40	ns
t _{OH}	Output Hold from Address Change	5	—	5	—	5	—	5	—	ns
Write Cycle										
t _{WC}	Write Cycle Time	55	—	70	—	85	—	100	—	ns
t _{WCW}	Chip Select to End of Write	50	—	60	—	70	—	80	—	ns
t _{AW}	Address Valid to End of Write	50	—	60	—	70	—	80	—	ns
t _{AS}	Address Set-up Time	0	—	0	—	0	—	0	—	ns
t _{WP}	Write Pulse Width	40	—	45	—	50	—	55	—	ns
t _{WR}	Write Recovery Time	0	—	0	—	0	—	0	—	ns
t _{WHZ}	Write Enable to Output in High Z ⁽²⁾	—	25	—	30	—	35	—	40	ns
t _{DW}	Data to Write Time Overlap	25	—	30	—	35	—	40	—	ns
t _{DH1}	Data Hold from Write Time (\overline{WE})	0	—	0	—	0	—	0	—	ns
t _{DH2}	Data Hold from Write Time (\overline{CS})	3	—	3	—	3	—	3	—	ns
t _{OW}	Output Active from End of Write ⁽²⁾	5	—	5	—	5	—	5	—	ns

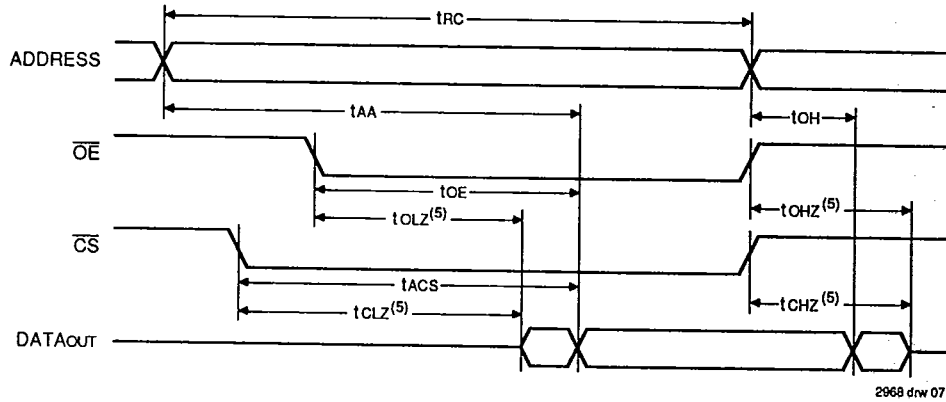
NOTES:

1. -55°C to +125°C temperature range only.
2. This parameter guaranteed but not tested.
3. 0° to +70°C temperature range only.
4. Also available: 120 and 150 ns military devices.
5. For the 0°C to +70°C temperature range,
 - 30ns speed grade, t_{OW} = 14ns.
 - 35ns speed grade, t_{OW} = 15ns.
 For the -55°C to +125°C temperature range,
 - 30ns speed grade, t_{OW} = 17ns.
 - 35ns speed grade, t_{OW} = 18ns.

2968 tbl 11

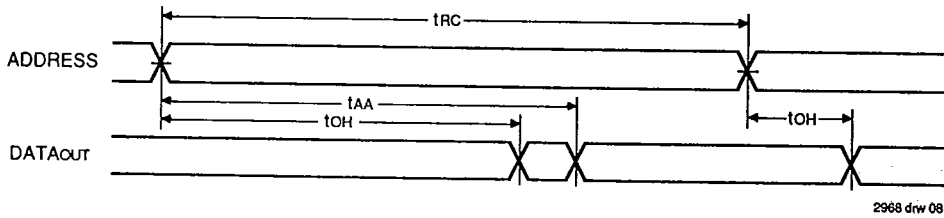
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TIMING WAVEFORM OF READ CYCLE NO. 1⁽¹⁾



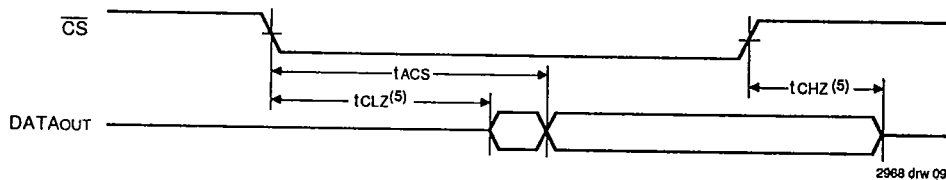
2968 drw 07

TIMING WAVEFORM OF READ CYCLE NO. 2^(1, 2, 4)



2968 drw 08

TIMING WAVEFORM OF READ CYCLE NO. 3^(1, 3, 4)

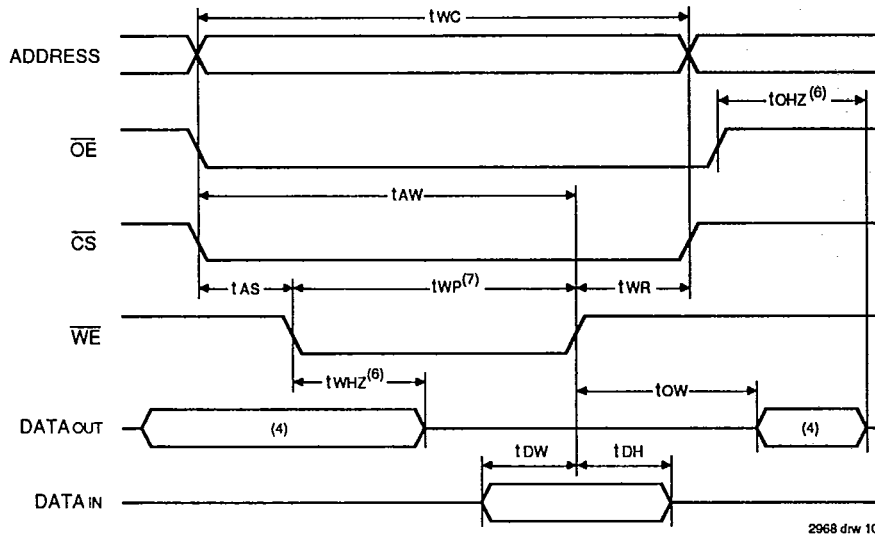


2968 drw 09

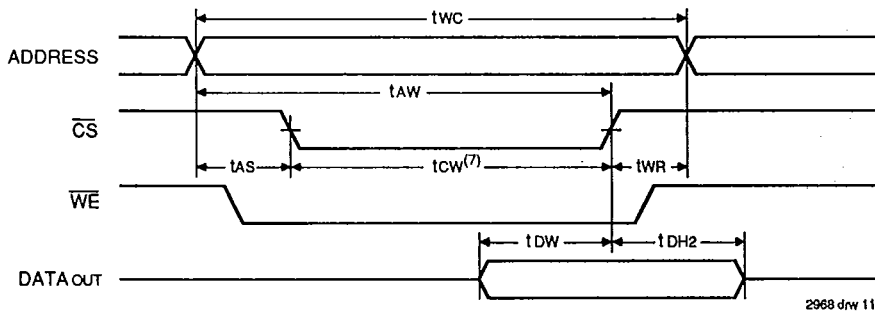
NOTES:

1. \overline{WE} is high for read cycle.
2. Device is continuously selected, $\overline{CS} = V_{IL}$.
3. Address valid prior to or coincident with \overline{CS} transition low.
4. $\overline{OE} = V_{IL}$.
5. Transition is measured $\pm 200mV$ from steady state with 5pF load (including scope and jig).

TIMING WAVEFORM OF WRITE CYCLE NO. 1 (\overline{WE} CONTROLLED TIMING)(1, 2, 3, 5, 7)



TIMING WAVEFORM OF WRITE CYCLE NO. 2 (\overline{CS} CONTROLLED TIMING)(1, 2, 3, 5)



NOTES:

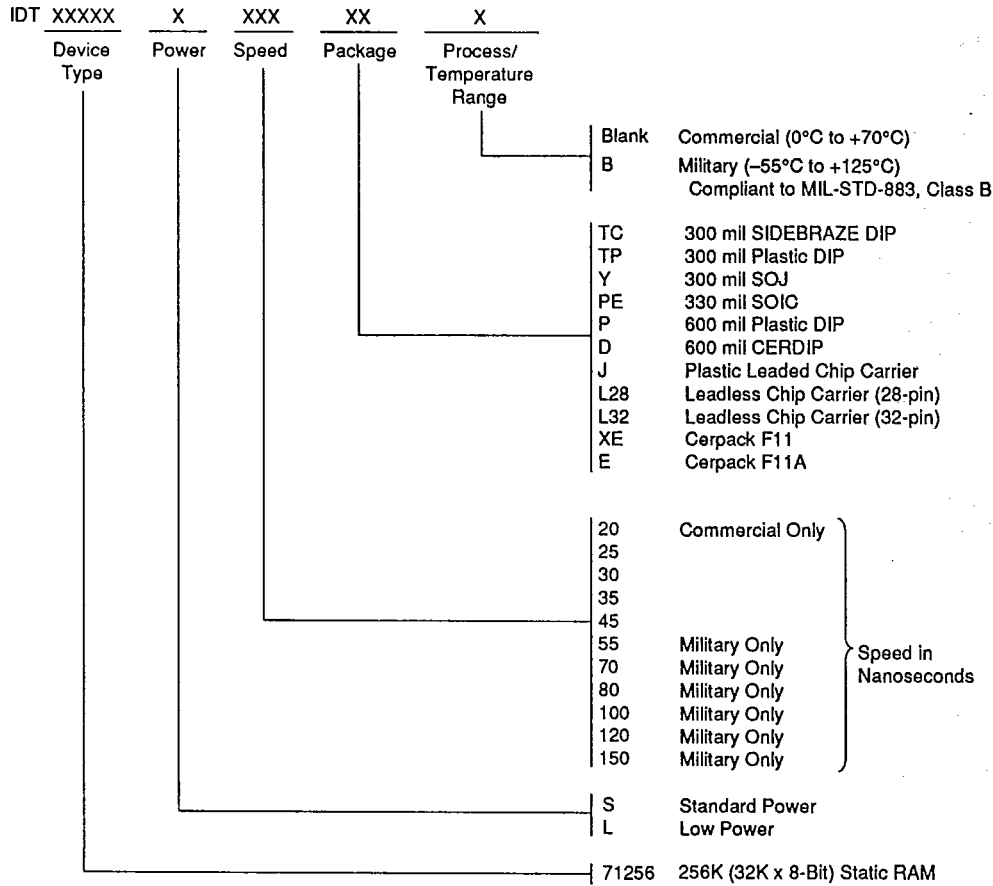
1. \overline{WE} or \overline{CS} must be high during all address transitions.
2. A write occurs during the overlap (t_{cw} or t_{wp}) of a low \overline{CS} and a low \overline{WE} .
3. t_{wr} is measured from the earlier of \overline{CS} or \overline{WE} going high to the end of the write cycle.
4. During this period, I/O pins are in the output state so that the input signals must not be applied.
5. If the \overline{CS} low transition occurs simultaneously with or after the \overline{WE} low transition, the outputs remain in a high impedance state.
6. Transition is measured $\pm 200\text{mV}$ from steady state with a 5pF load (including scope and jig).
7. If \overline{OE} is low during a \overline{WE} controlled write cycle, the write pulse width must be the larger of t_{wp} or ($t_{whz} + t_{dw}$) to allow the I/O drivers to turn off and data to be placed on the bus for the required t_{dw} . If \overline{OE} is high during a \overline{WE} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{wp} .

IDT71256 CMOS STATIC RAM 256K (32K x 8-BIT)

MILITARY AND COMMERCIAL TEMPERATURE RANGES

ORDERING INFORMATION

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